

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SC5353

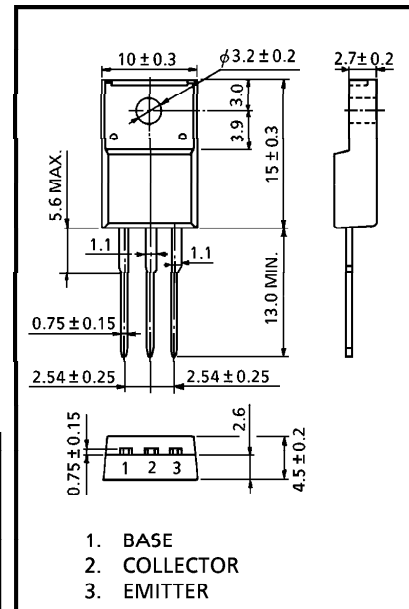
SWITCHING REGULATOR AND HIGH VOLTAGE SWITCHING APPLICATIONS
HIGH SPEED DC-DC CONVERTER APPLICATIONS

- Excellent Switching Times
: $t_r=0.7\mu s$ (Max.), $t_f=0.5\mu s$ (Max.)
- High Collectors Breakdown Voltage : $V_{CEO}=800V$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	900	V
Collector-Emitter Voltage	V_{CEO}	800	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	DC	I_C	3
	Pulse	I_{CP}	5
Base Current	I_B	1	A
Collector Power Dissipation	$T_a=25^\circ C$	P_C	2.0
	$T_c=25^\circ C$		25
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Unit in mm



JEDEC	—
EIAJ	SC-67
TOSHIBA	2-10R1A

Weight : 1.7g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 720V, I_E = 0$	—	—	100	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 7V, I_C = 0$	—	—	10	μA
Collector-Base Breakdown Voltage		$V_{(BR) CBO}$	$I_C = 1mA, I_E = 0$	900	—	—	V
Collector-Emitter Breakdown Voltage		$V_{(BR) CEO}$	$I_C = 10mA, I_B = 0$	800	—	—	V
DC Current Gain		$h_{FE} (1)$	$V_{CE} = 5V, I_C = 1mA$	10	—	—	
		$h_{FE} (2)$	$V_{CE} = 5V, I_C = 0.15A$	15			
Collector-Emitter Saturation Voltage		$V_{CE} (sat)$	$I_C = 1.2A, I_B = 0.24A$	—	—	1.0	V
Base-Emitter Saturation Voltage		$V_{BE} (sat)$	$I_C = 1.2A, I_B = 0.24A$	—	—	1.3	V
Switching Time	Rise Time	t_r	<p> $I_{B1} = 0.24A, I_{B2} = -0.48A$ DUTY CYCLE $\leq 1\%$ </p>	—	—	0.7	μs
	Storage Time	t_{stg}		—	—	4.0	
	Fall Time	t_f		—	—	0.5	

